



# CPH6337 — General-Purpose Switching Device Applications

P-Channel Silicon MOSFET

## Features

- Ultrahigh-speed switching
- 1.8V drive

## Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		-12	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±10	V
Drain Current (DC)	I <sub>D</sub>		-3.5	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	-14	A
Allowable Power Dissipation	P <sub>D</sub>	When mounted on ceramic substrate (1200mm <sup>2</sup> ×0.8mm)	1.6	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

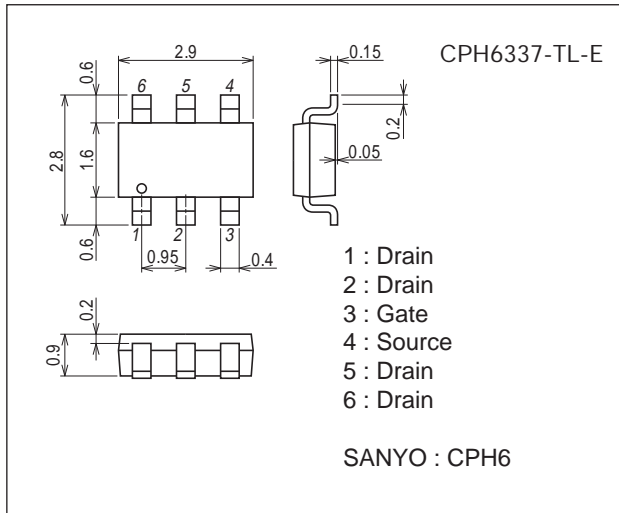
This product is designed to "ESD immunity < 200V\*\*", so please take care when handling.

\* Machine Model

## Package Dimensions

unit : mm (typ)

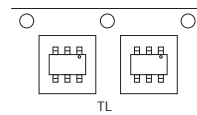
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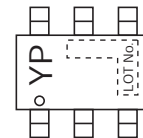
## Product & Package Information

- Package : CPH6
- JEITA, JEDEC : SC-74, SOT-26, SOT-457
- Minimum Packing Quantity : 3,000 pcs./reel

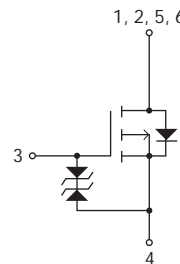
## Packing Type: TL



## Marking



## Electrical Connection

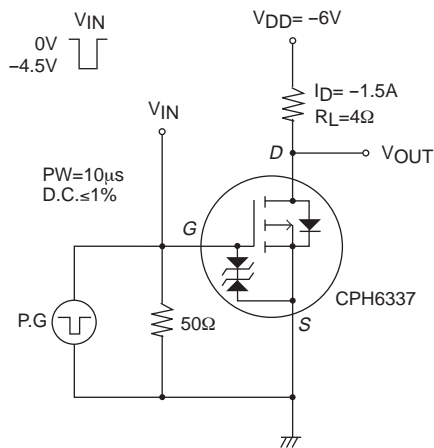


# CPH6337

## Electrical Characteristics at Ta=25°C

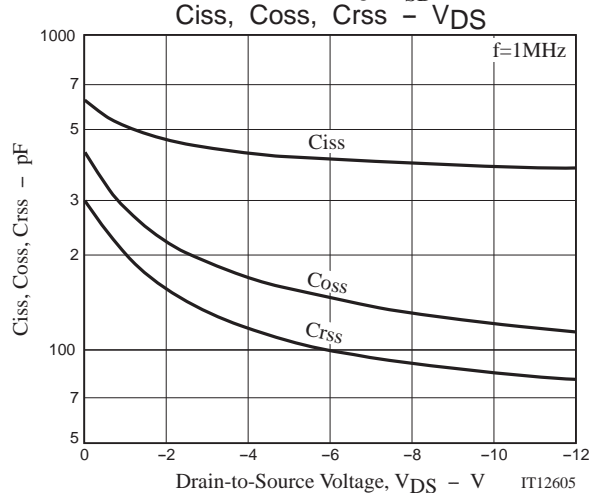
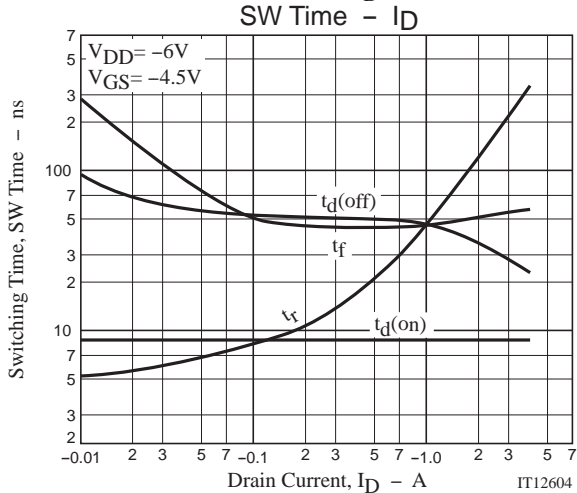
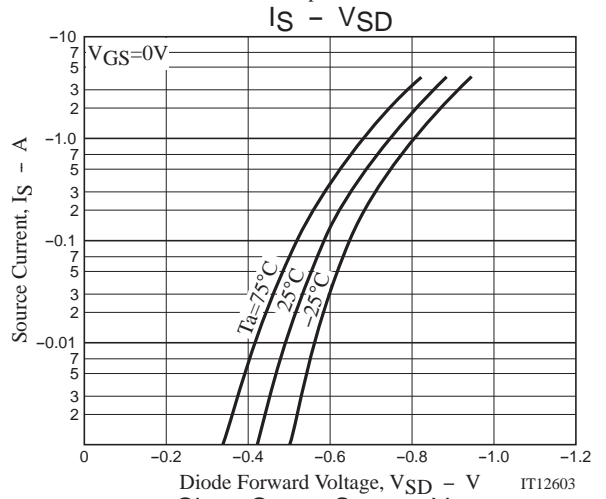
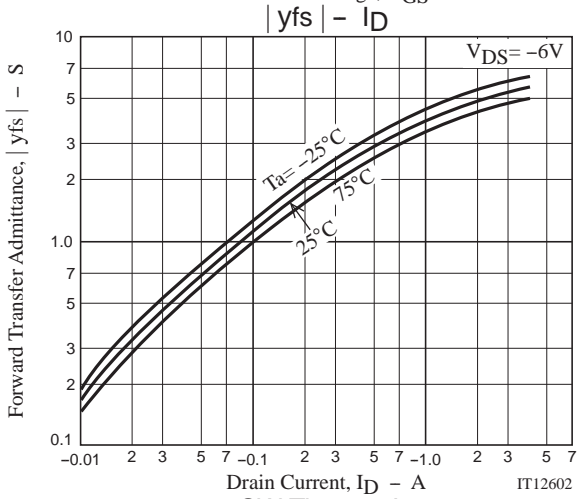
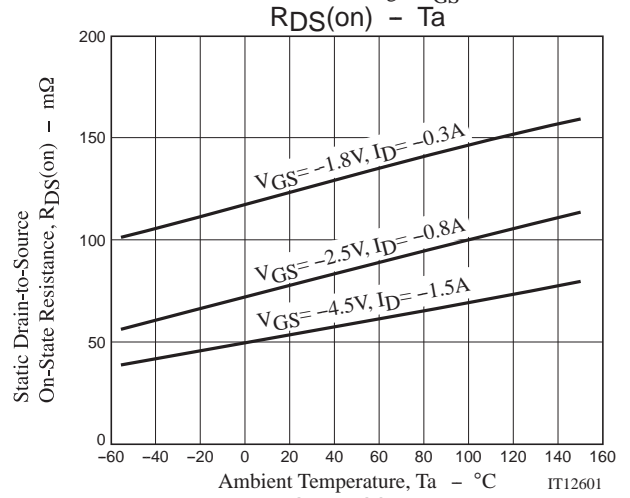
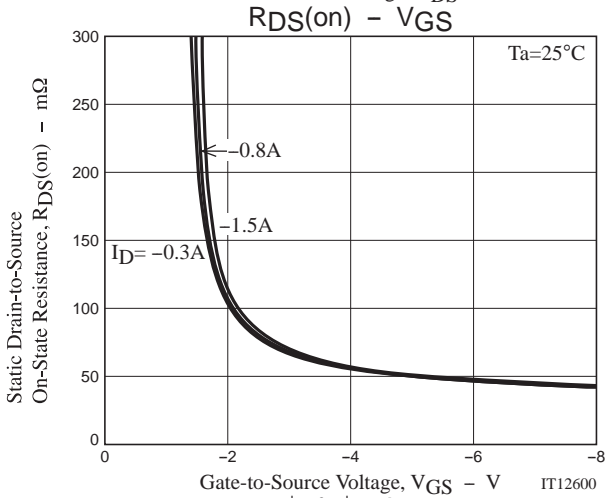
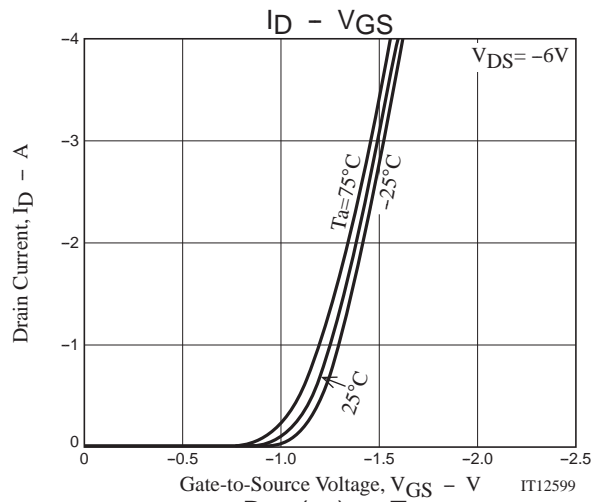
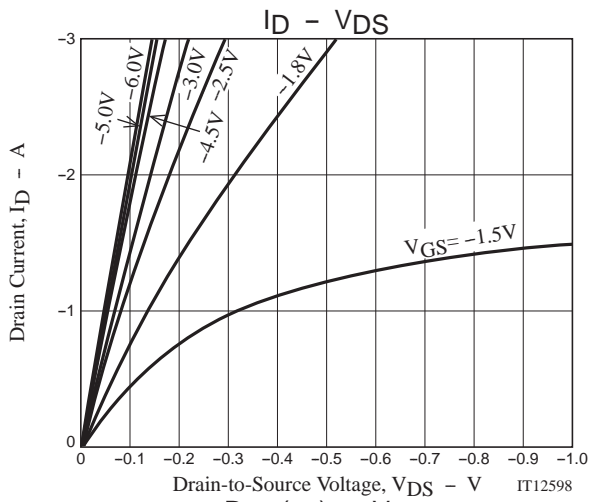
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =-1mA, V <sub>GS</sub> =0V	-12			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-12V, V <sub>GS</sub> =0V			-10	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =-6V, I <sub>D</sub> =-1mA	-0.4		-1.4	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =-6V, I <sub>D</sub> =-1.5A	2.7	4.5		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =-1.5A, V <sub>GS</sub> =-4.5V		54	70	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =-0.8A, V <sub>GS</sub> =-2.5V		80	115	mΩ
	R <sub>DS(on)3</sub>	I <sub>D</sub> =-0.3A, V <sub>GS</sub> =-1.8V		125	215	mΩ
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-6V, f=1MHz		405		pF
Output Capacitance	C <sub>oss</sub>			145		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			100		pF
Turn-ON Delay Time	t <sub>d(on)</sub>			8.8		ns
Rise Time	t <sub>r</sub>	See specified Test Circuit.		80		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>			41		ns
Fall Time	t <sub>f</sub>			50		ns
Total Gate Charge	Q <sub>g</sub>			5.6		nC
Gate-to-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =-6V, V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3.5A		0.7		nC
Gate-to-Drain "Miller" Charge	Q <sub>gd</sub>			1.6		nC
Diode Forward Voltage	V <sub>SD</sub>		I <sub>S</sub> =-3.5A, V <sub>GS</sub> =0V		-0.86	-1.5

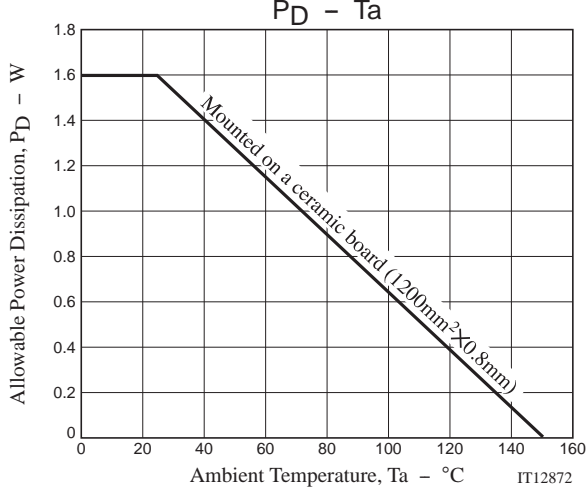
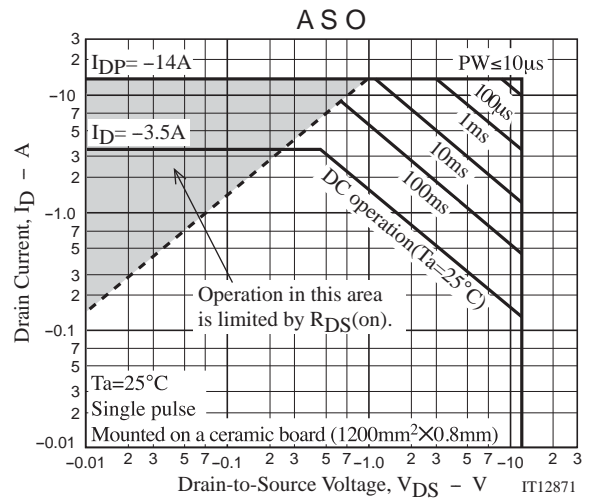
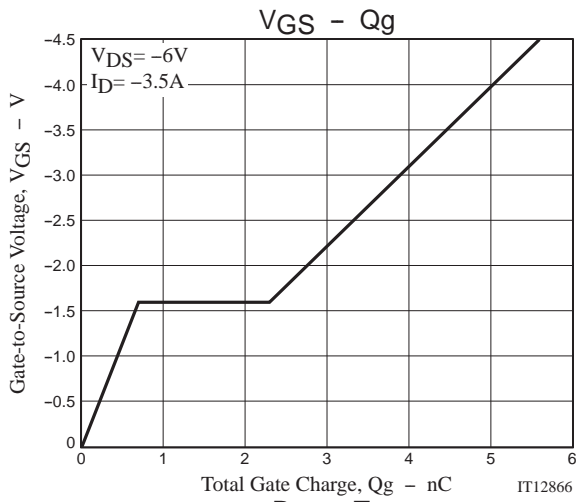
## Switching Time Test Circuit



## Ordering Information

Device	Package	Shipping	memo
CPH6337-TL-E	CPH6	3,000pcs./reel	Pb Free





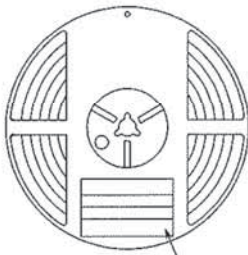
Embossed Taping Specification

CPH6337-TL-E

1. Packing Format

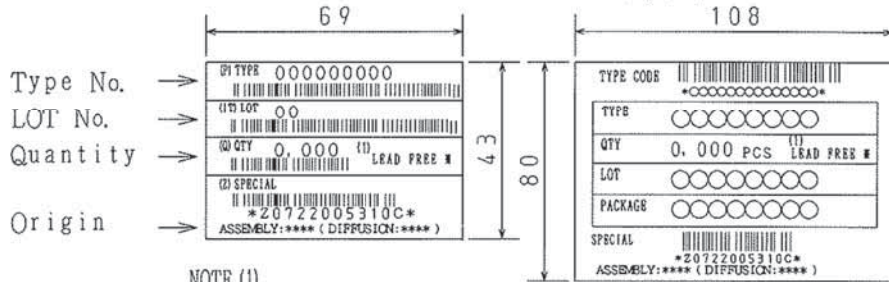
Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
CPH6	CPH6	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

Packing method



Reel label

Reel label, Inner box label (unit:mm)      Outer box label  
It is a label at the time of factory shipments. The form of a label may change in physical distribution process.



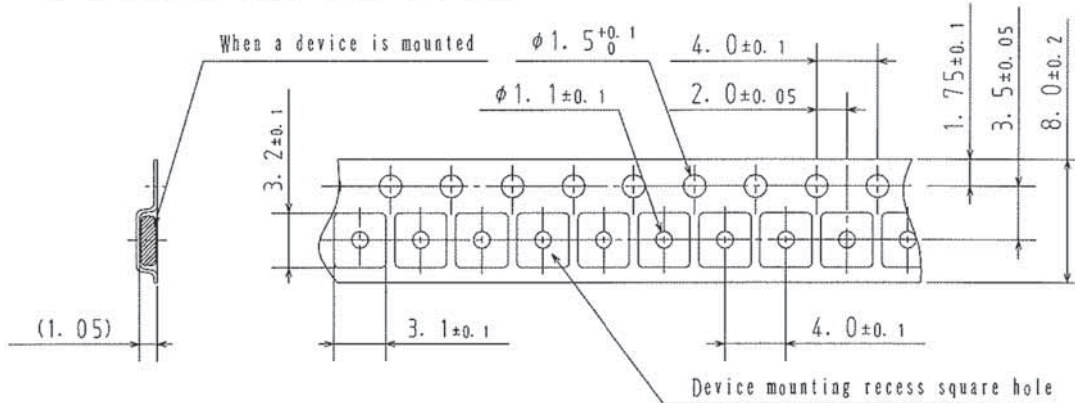
NOTE (1)

The LEAD FREE \* description shows that the surface treatment of the terminal is lead free.

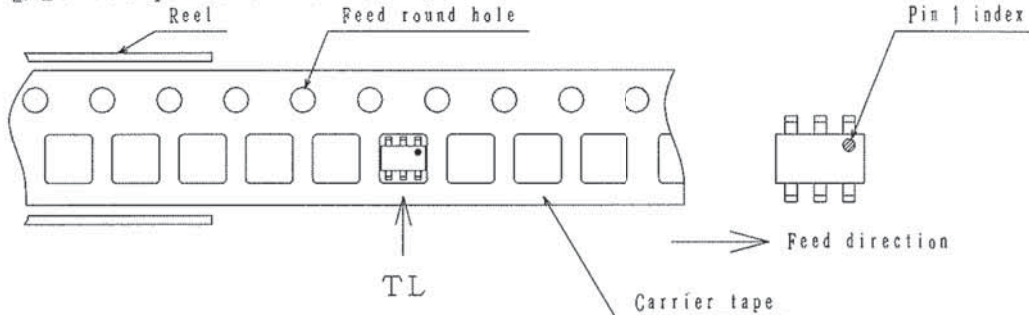
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



2-2. Device placement direction

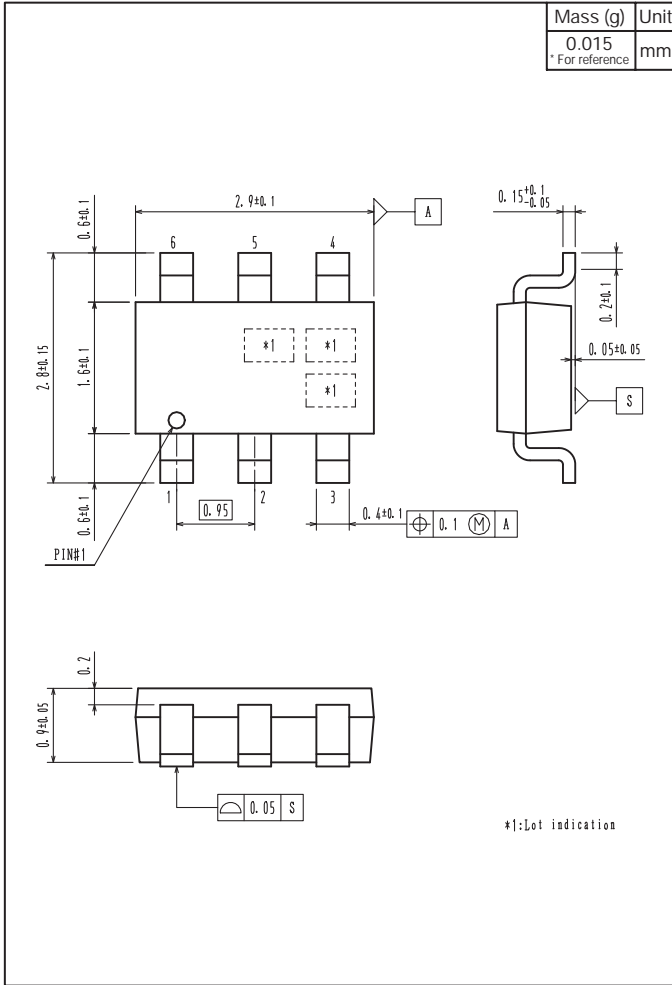


Those with pin 1 index on the feed hole side.....TL

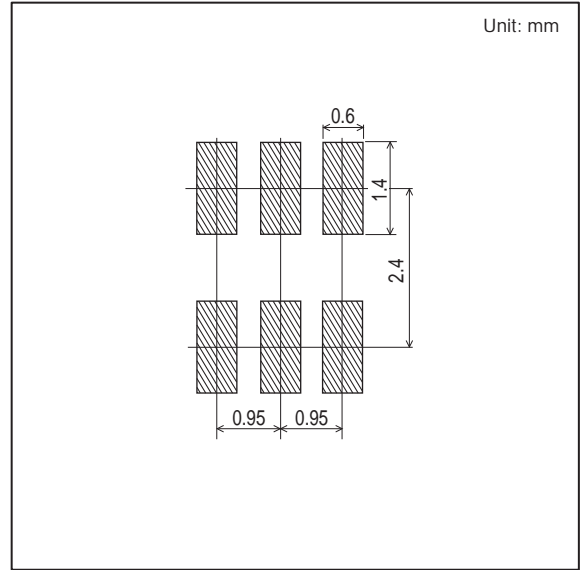
# CPH6337

## Outline Drawing

CPH6337-TL-E



## Land Pattern Example



Note on usage : Since the CPH6337 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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